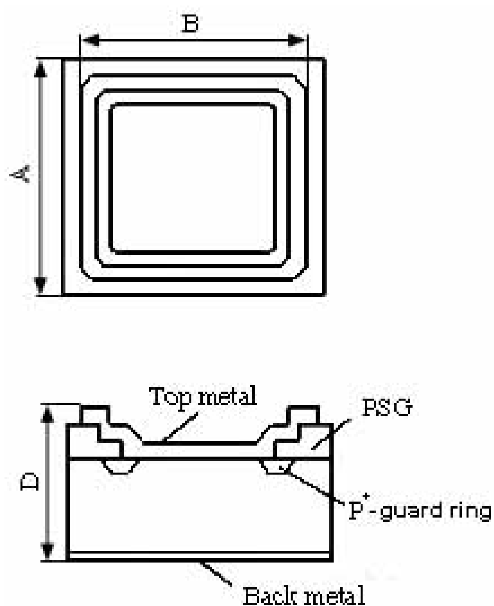
Sep. 2013

SCHOTTKY DIODES KDS-03040I.

RoHS

VSP-MIKRON	**3A/40V. Die Size-65mil.**			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25˚C, I_F=3,0A	V_F	V	0,40	0,38 (0,37-typ)
Maximum Reverse Current @ 25˚C, V_R=40V 25˚C, V_R=42V 100˚C, V_R=40V	I_R	mA	0,5 - 50,0	0,45 0,5 45,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	110	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<125˚C.	I_{RRM}	A	2,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	125	



DIM	**ITEM**	**µm**
A_X A_y	Wafer Form Die Size	1650 1650
B_X B_y	Top Metal Size	1470 1470
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;

b) ***Al-Ni-Ag*** – for Soldering.

Backside metal: ***Ti-Ni-Ag***.